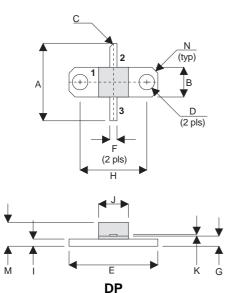
### TetraFET

# D2210UK



## ROHS COMPLIANT METAL GATE RF SILICON FET

#### **MECHANICAL DATA**



PIN 1	SOURCE	PIN 2	DRAIN
PIN 3	GATE		

DIM	mm	Tol.	Inches	Tol.
Α	16.51	0.25	0.650	0.010
В	6.35	0.13	0.250	0.005
С	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.08	0.745	0.003
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
Н	14.22	0.08	0.560	0.003
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.13	0.03	0.005	0.001
Μ	5.08	0.51	0.200	0.020
Ν	1.27 x 45°	0.13	0.050 x 45°	0.005

## GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 20W – 12.5V – 500MHz SINGLE ENDED

#### **FEATURES**

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C<sub>rss</sub>
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 10 dB MINIMUM

### **APPLICATIONS**

• VHF/UHF COMMUNICATIONS from DC to 1 GHz

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C unless otherwise stated)

P <sub>D</sub>	Power Dissipation	70W
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage	40V
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage	±20V
I <sub>D(sat)</sub>	Drain Current	16A
T <sub>stg</sub>	Storage Temperature	–65 to 150°C
Тj	Maximum Operating Junction Temperature	200°C



## D2210UK

## **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$ unless otherwise stated)

	Parameter	Test Conditions			Min.	Тур.	Max.	Unit
B\/	Drain-Source	V <sub>GS</sub> = 0	I <sub>D</sub> = 1	٥m٨	40			V
BV <sub>DSS</sub>	Breakdown Voltage	VGS – U	1D – 1		40			v
	Zero Gate Voltage	V - 12 5V		0			8	mA
IDSS	Drain Current	$V_{DS} = 12.5V$ $V_{GS} =$		S = 0			0	ШA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = 20V	V <sub>DS</sub> =	0			8	μΑ
V <sub>GS(th)</sub>	Gate Threshold Voltage*	I <sub>D</sub> = 10mA	V <sub>DS</sub> =	V <sub>GS</sub>	0.5		7	V
9 <sub>fs</sub>	Forward Transconductance*	V <sub>DS</sub> = 10V	I <sub>D</sub> = 1	.6A	1.44			S
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 20W			10			dB
η	Drain Efficiency	V <sub>DS</sub> = 12.5V	I <sub>DQ</sub> =	1.6A	40			%
VSWR	Load Mismatch Tolerance	f = 500MHz			20:1			
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 12.5V V	/ <sub>GS</sub> = -5V f	= 1MHz			96	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 12.5V V	$I_{GS} = 0$ f	= 1MHz			80	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 12.5V V	/ <sub>GS</sub> = 0 f	= 1MHz			8	pF

\* Pulse Test: Pulse Duration = 300  $\mu s$  , Duty Cycle  $\leq 2\%$ 

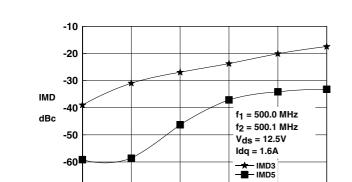
#### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

#### THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

#### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 2.5°C / W
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Figure 1 – Gain vs. Power Output.

Pout W

Figure 3 – IMD vs. Power Output.

Pout W PEP

15

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## **Typical S Parameters**

#### ! V<sub>DS</sub> = 12.5V, I<sub>DQ</sub> = 0.8A # MHZ S MA R 50

25

30

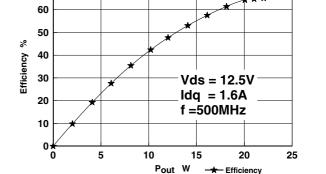
!Freq MHz	S11 mag	ang	S21 mag	ang	S12 mag	ang	S22 mag	ang
100	0.82	-160	9.92	72	0.018	-12	0.7	-155
200	0.88	-169	3.92	50	0.011	-16	0.81	-162
300	0.91	-175	2.29	40	0.006	11	0.87	-169
400	0.93	-179	1.43	30	0.008	57	0.91	-175
500	0.95	178	1.03	23	0.013	77	0.93	-179
600	0.95	173	0.76	14	0.019	78	0.95	176
700	0.95	170	0.56	7	0.023	75	0.96	173
800	0.96	166	0.39	5	0.025	76	0.97	169
900	0.97	163	0.33	9	0.032	84	0.97	166
1000	0.98	158	0.3	7	0.041	78	0.97	162

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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#### D2210UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency	Z <sub>S</sub>	ZL
MHz	Ω	Ω
500MHz	1.4 + j1.1	2.4 – j0.4

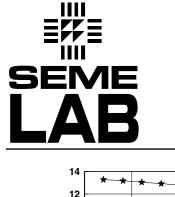
Vds = 12.5V Idq = 1.6A f =500MHz

15

20

– Gain

25



10

8

6

4

2

0

-70

5

0

5

10

Gain dB



## D2210UK

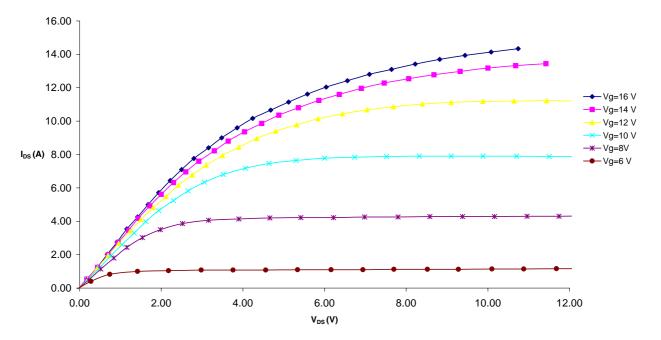
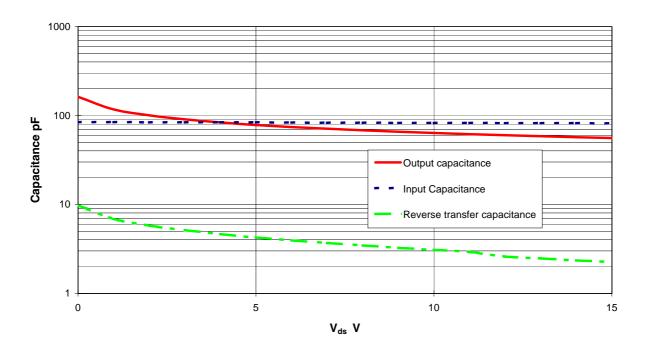


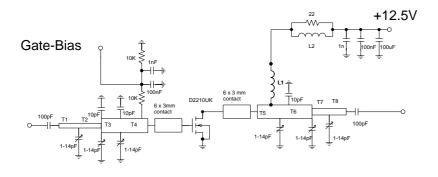
Figure 4 – Typical IV Characteristics.





# D2210UK

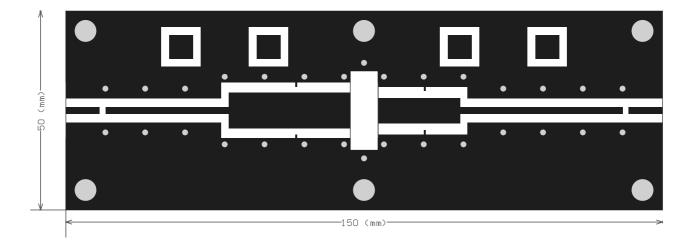




# D2210UK 500MHz TEST FIXTURE

Substrate Taconic RF35 0.8mm, Er=3.5

- T1 1.68mm wide, 21mm long
- T2 1.68mm wide, 104mm long
- T3 8.92mm wide, 17mm long
- T4 8.92mm wide, 13.5mm long
- T5 6.34mm wide, 11.5mm long
- T6 6.34mm wide, 9mm long
- T7 1.68mm wide, 13mm long
- T8 1.68mm wide, 28mm long
- L1 10 turns 0.5mm dia enamelled copper wire, 3mm i.d.
- L2 1.5 turns 0.5mm dia enamelled copper wire on Siemens B62152-A7X ferrite core



#### Artwork